30 V, 1.5 A ultra low V_F MEGA Schottky barrier rectifiers

Rev. 03 — 13 January 2010

Product data sheet

1. Product profile

1.1 General description

Planar Maximum Efficiency General Application (MEGA) Schottky barrier rectifiers with an integrated guard ring for stress protection, encapsulated in small and flat lead SMD plastic packages.

Table 1. Product overview

Type number	Package		Configuration
	NXP	JEITA	
PMEG3015EH	SOD123F	-	single diode
PMEG3015EJ	SOD323F	SC-90	single diode

1.2 Features

Forward current: ≤ 1.5 A

Reverse voltage: ≤ 30 V

Ultra low forward voltage

Small and flat lead SMD plastic packages

1.3 Applications

- Low voltage rectification
- High efficiency DC-to-DC conversion
- Switch mode power supply
- Inverse polarity protection
- Low power consumption applications

1.4 Quick reference data

Table 2. Quick reference data

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
I _F	forward current	$T_{sp} \leq 55 ^{\circ}C$	-	-	1.5	Α
V_R	reverse voltage		-	-	30	V
V _F	forward voltage	I _F = 1.5 A	<u>[1]</u> _	440	550	mV

[1] Pulse test: $t_p \leq 300~\mu s;~\delta \leq 0.02.$



30 V, 1.5 A ultra low V_F MEGA Schottky barrier rectifiers

2. Pinning information

Table 3. Pinning

	3	
Pin	Description	Simplified outline Symbol
1	cathode	[1]
2	anode	1 2 2 sym001
		001aab540

^[1] The marking bar indicates the cathode.

3. Ordering information

Table 4. Ordering information

Type number	Package		
	Name	Description	Version
PMEG3015EH	-	plastic surface mounted package; 2 leads	SOD123F
PMEG3015EJ	SC-90	plastic surface mounted package; 2 leads	SOD323F

4. Marking

Table 5. Marking codes

•	
Type number	Marking code
PMEG3015EH	AE
PMEG3015EJ	EK

5. Limiting values

Table 6. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Max	Unit
V_{R}	reverse voltage		-	30	V
I _F	forward current	$T_{sp} \le 55 ^{\circ}C$	-	1.5	Α
I _{FRM}	repetitive peak forward current	$t_p \le 1$ ms; $\delta \le 0.25$	-	4.5	Α
I _{FSM}	non-repetitive peak forward current	square wave; t _p = 8 ms	-	9	Α
P _{tot}	total power dissipation	$T_{amb} \le 25 ^{\circ}C$			
	PMEG3015EH		<u>[1]</u> _	375	mW
			[2] _	830	mW
	PMEG3015EJ		<u>[1]</u> _	360	mW
			[2] _	830	mW
Tj	junction temperature		-	150	°C

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30 V, 1.5 A ultra low V_F MEGA Schottky barrier rectifiers

Table 6. Limiting values continued

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Max	Unit
T _{amb}	ambient temperature		-65	+150	°C
T _{stg}	storage temperature		-65	+150	°C

^[1] Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated and standard footprint.

6. Thermal characteristics

Table 7. Thermal characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
$R_{\text{th(j-a)}}$	thermal resistance from junction to ambient	in free air				
	PMEG3015EH	[1]	[2] _	-	330	K/W
		[2]	[3] _	-	150	K/W
	PMEG3015EJ	[1]	[2] _	-	350	K/W
		[2]	[3] _	-	150	K/W
R _{th(j-sp)}	thermal resistance from junction to solder point					
	PMEG3015EH		-	-	60	K/W
	PMEG3015EJ		-	-	55	K/W

^[1] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.

7. Characteristics

Table 8. Characteristics

 T_{amb} = 25 °C unless otherwise specified.

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
V_{F}	forward voltage	I _F = 1 mA	<u>[1]</u> _	125	160	mV
		I _F = 10 mA	[1] _	185	220	mV
		I _F = 100 mA	[1] _	255	290	mV
		I _F = 500 mA	<u>[1]</u> _	330	380	mV
		I _F = 1 A	<u>[1]</u> _	400	480	mV
		I _F = 1.5 A	<u>[1]</u> _	440	550	mV
I_R	reverse current	V _R = 10 V	-	60	150	μΑ
		V _R = 30 V	-	400	1000	μΑ
C_{d}	diode capacitance	$V_R = 1 V$; $f = 1 MHz$	-	60	72	pF

^[1] Pulse test: $t_p \le 300~\mu s;~\delta \le 0.02.$

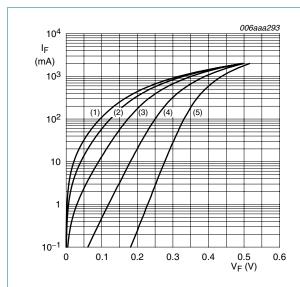
PMEG3015EH_EJ_3

^[2] Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for cathode 1cm².

^[2] For Schottky barrier diodes thermal run-away has to be considered, as in some applications the reverse power losses P_R are a significant part of the total power losses. Nomograms for determining the reverse power losses P_R and I_{F(AV)} rating are available on request.

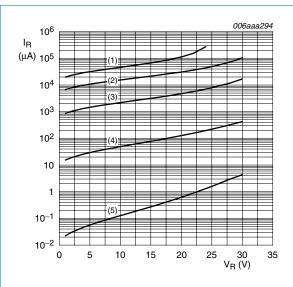
^[3] Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for cathode 1cm².

30 V, 1.5 A ultra low V_F MEGA Schottky barrier rectifiers



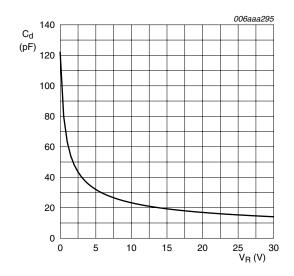
- (1) $T_{amb} = 150 \, ^{\circ}C$
- (2) T_{amb} = 125 °C
- (3) $T_{amb} = 85 \, ^{\circ}C$
- (4) $T_{amb} = 25 \, ^{\circ}C$
- (5) $T_{amb} = -40 \, ^{\circ}C$

Fig 1. Forward current as a function of forward voltage; typical values



- (1) T_{amb} = 150 °C
- (2) T_{amb} = 125 °C
- (3) $T_{amb} = 85 \, ^{\circ}C$
- (4) $T_{amb} = 25 \,^{\circ}C$
- (5) $T_{amb} = -40 \, ^{\circ}C$

Fig 2. Reverse current as a function of reverse voltage; typical values

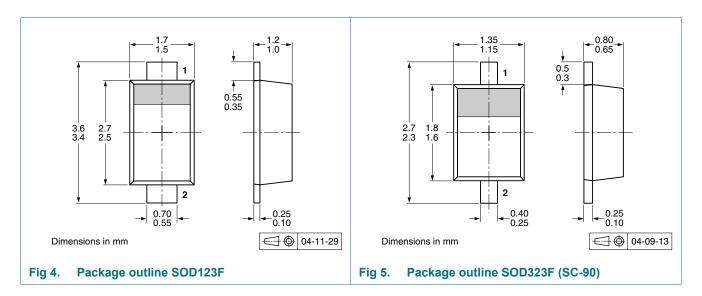


 T_{amb} = 25 °C; f = 1 MHz

Fig 3. Diode capacitance as a function of reverse voltage; typical values

30 V, 1.5 A ultra low V_F MEGA Schottky barrier rectifiers

8. Package outline



9. Packing information

Table 9. Packing methods

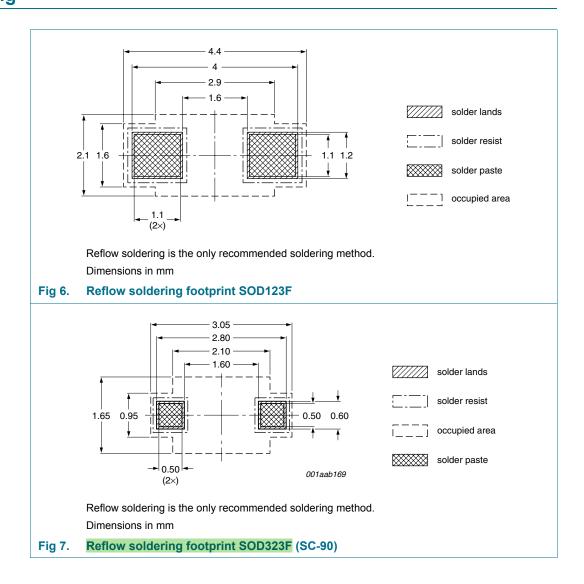
The indicated -xxx are the last three digits of the 12NC ordering code.[1]

Type number	Package	Description	Packing of	Packing quantity		
			3000	10000		
PMEG3015EH	SOD123F	4 mm pitch, 8 mm tape and reel	-115	-135		
PMEG3015EJ	SOD323F					

[1] For further information and the availability of packing methods, see <u>Section 13</u>.

30 V, 1.5 A ultra low $\overline{V_F}$ MEGA Schottky barrier rectifiers

10. Soldering



30 V, 1.5 A ultra low V_F MEGA Schottky barrier rectifiers

11. Revision history

Table 10. Revision history

Document ID	Release date	Data sheet status	Change notice	Supersedes
PMEG3015EH_EJ_3	20100113	Product data sheet	-	PMEG3015EH_EJ_2
Modifications:	 This data sheet was changed to reflect the new company name NXP Semiconductors, including new legal definitions and disclaimers. No changes were made to the technical content. 			
PMEG3015EH_EJ_2	20050408	Product data sheet	-	PMEG3015EJ_1
PMEG3015EJ_1	20050303	Product data sheet	-	-

30 V, 1.5 A ultra low V_F MEGA Schottky barrier rectifiers

12. Legal information

12.1 Data sheet status

Document status[1][2]	Product status[3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

- [1] Please consult the most recently issued document before initiating or completing a design.
- [2] The term 'short data sheet' is explained in section "Definitions"
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8 of 9

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30 V, 1.5 A ultra low V_F MEGA Schottky barrier rectifiers

14. Contents

1	Product profile	1
1.1	General description	1
1.2	Features	
1.3	Applications	1
1.4	Quick reference data	1
2	Pinning information	2
3	Ordering information	2
4	Marking	2
5	Limiting values	2
6	Thermal characteristics	3
7	Characteristics	3
8	Package outline	5
9	Packing information	5
10	Soldering	6
11	Revision history	7
12	Legal information	8
12.1	Data sheet status	8
12.2	Definitions	8
12.3	Disclaimers	8
12.4	Trademarks	8
13	Contact information	8
11	Contents	۵

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